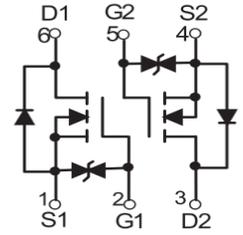




MMBT7002KV Plastic-Encapsulate MOSFETS

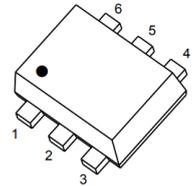
N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60 V	5Ω @10V	340mA
	5.3Ω @4.5V	



FEATURE

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected



SOT563

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING : 72K

MOSFET MAXIMUM RATINGS ($T_a=25\text{Я}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	340	mA
I_{DM}	Pulsed Drain Current(note1)	800	mA
P_D	Power Dissipation	0.2	W
T_j	Junction Temperature	150	Я
T_{stg}	Storage Temperature	-55~+150	Я
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	Я/W



MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^{\circ}\text{C}$ unless otherwise specified

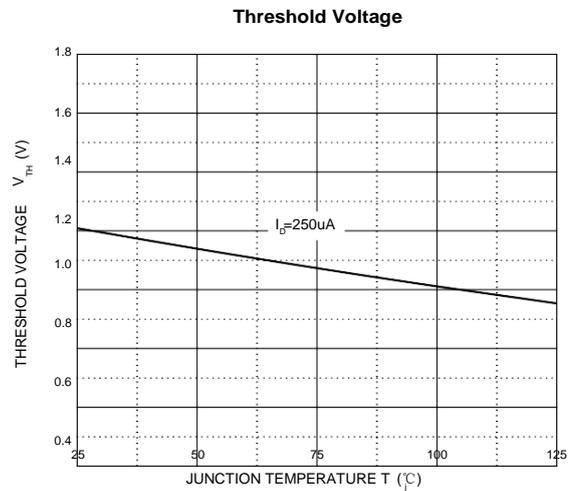
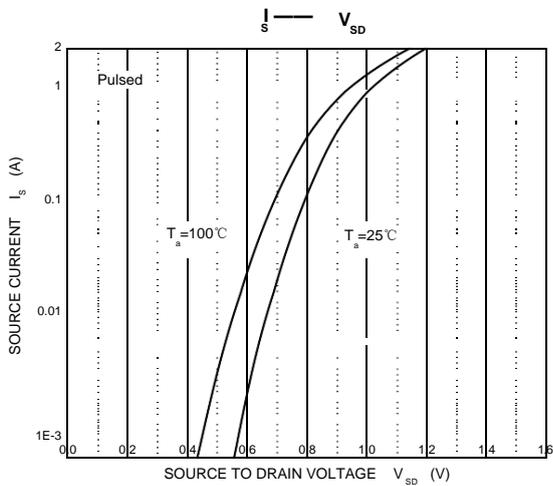
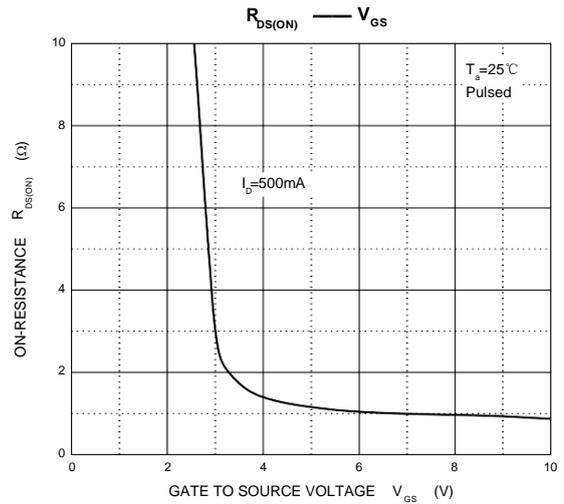
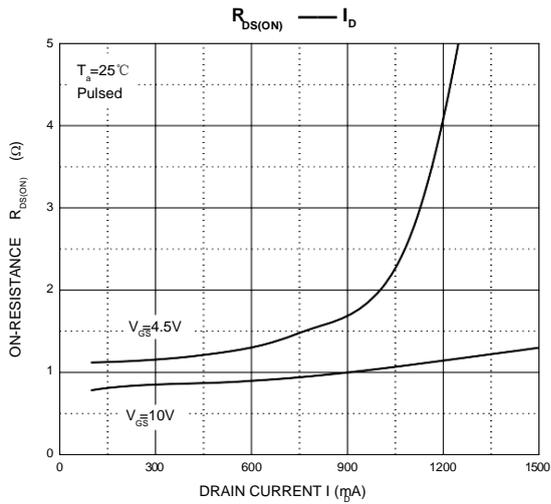
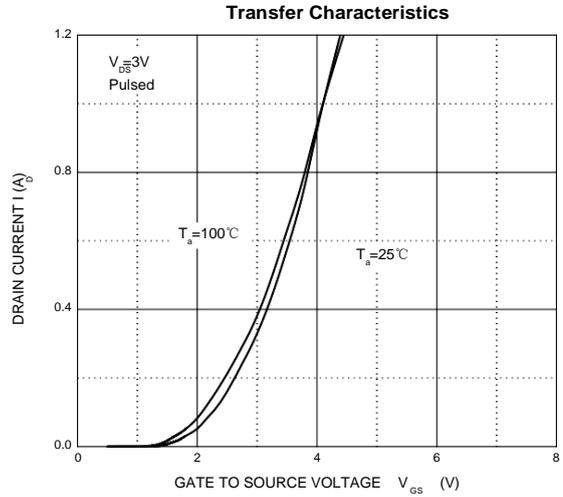
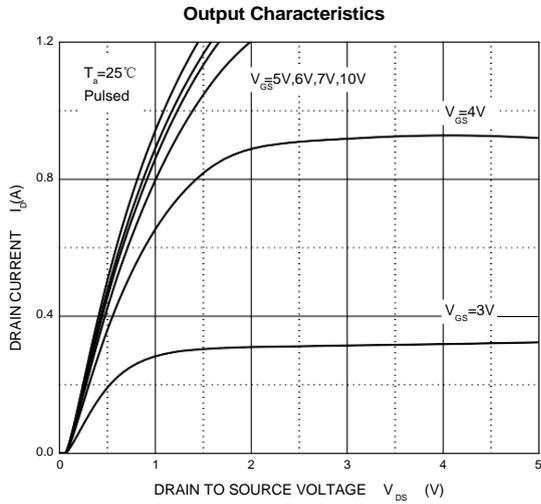
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
GateThreshold Voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
Drain-Source On-Resistance (note 2)	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 200mA$		2.3	5.3	R
		$V_{GS} = 10V, I_D = 500mA$		1.5	5	R
DYNAMIC PARAMETERS (note 3)						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
SWITCHING PARAMETERS (note 3)						
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega$			10	ns
Turn-off Delay Time	$t_{d(off)}$	$R_{GS} = 50\Omega, R_L = 250\Omega$			15	ns
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu s$		30		ns
Recovered Charge	Q_r	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu s$		30		nC
DRAIN-SOURCE DIODE						
Diode Forward Voltage(note 2)	V_{SD}	$I_S = 300mA, V_{GS} = 0V$			1.5	V
Continuous Diode Forward Current	I_S				0.2	A
Pulsed Diode Forward Current(note1)	I_{SM}				0.53	A

Notes :

1. Repetitive rating -- Pulse width limited by junction temperature.
2. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production testing.

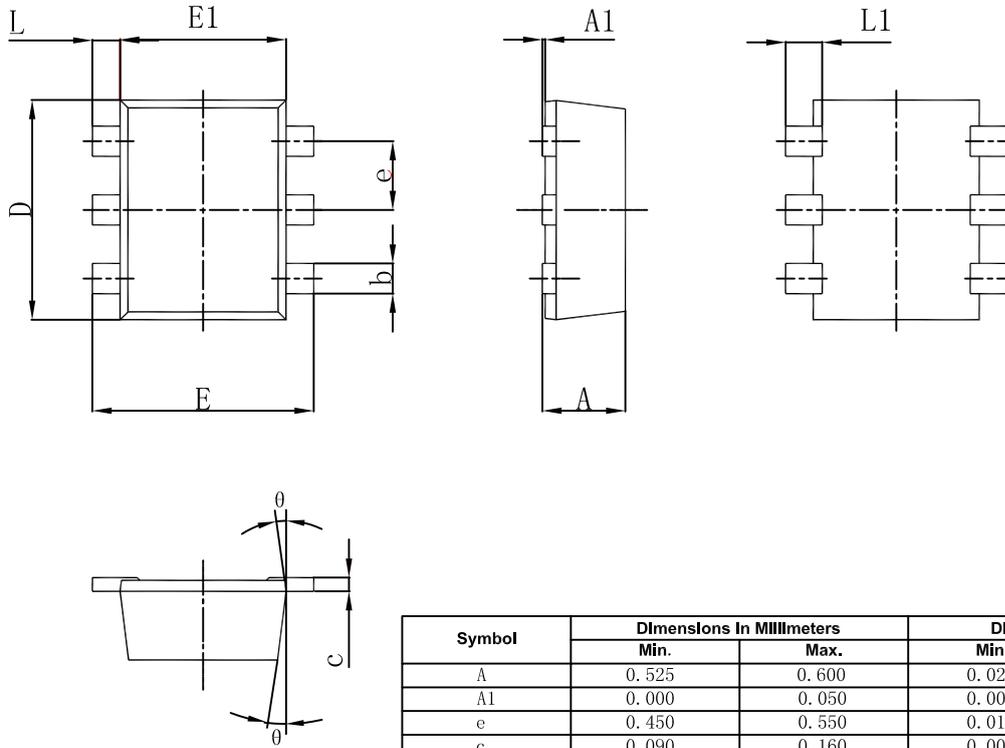


Typical Characteristics



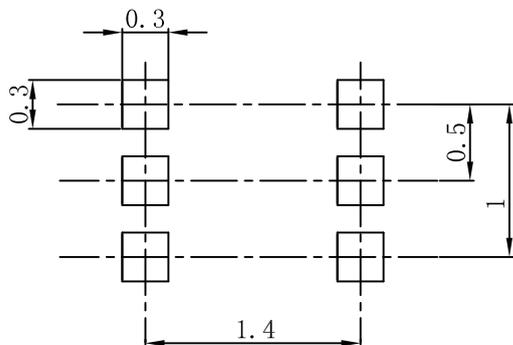


SOT-563 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7 °REF.		7 °REF.	

SOT-563 Suggested Pad Layout

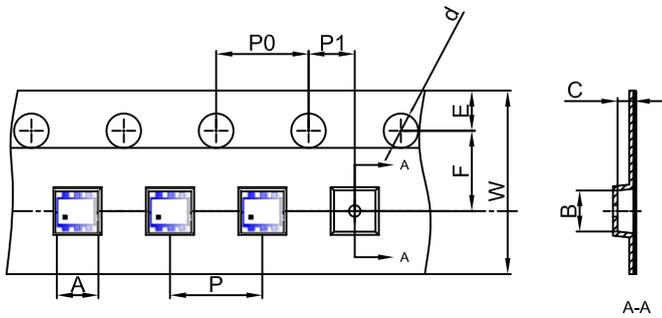


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



SOT-563 Embossed Carrier Tape



Packaging Description:
 SOT-563 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-563	1.78	1.78	0.69	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-563 Tape Leader and Trailer

